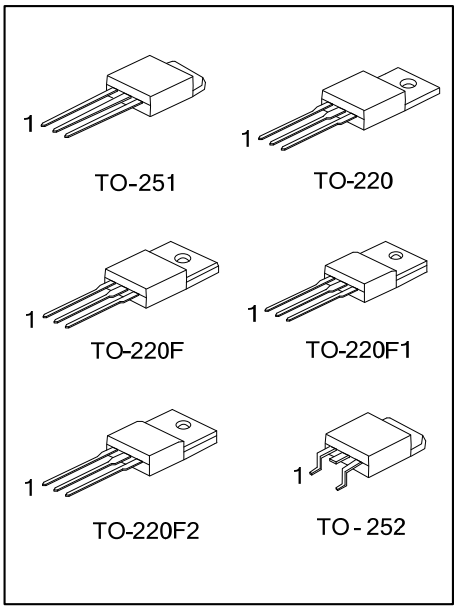
18NM65

Power MOSFET

18A, 650V N-CHANNEL SUPER-JUNCTION MOSFET



■ DESCRIPTION

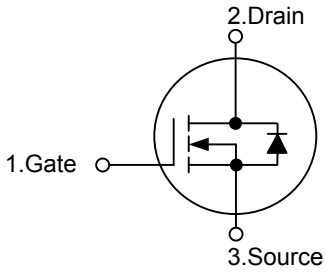
The UTC **18NM65** is a high voltage super junction MOSFET and is designed to have better characteristics.

The UTC **18NM65** Utilizing an advanced charge-balance technology, enhance system efficiency, improve EMI and reliability. such as low gate charge, low on-state resistance and have a high power density and high rugged avalanche characteristics. This super junction MOSFET usually used at AC/DC power conversion, and industrial power applications.

■ FEATURES

* $R_{DS(ON)}$ < 0.33Ω @ V_{GS}=10V, I_D=9.0A
* Fast Switching Capability
* Avalanche Energy Specified
* Improved dv/dt Capability, High Ruggedness

■ SYMBOL



■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
18NM65L-TA3-T	18NM65G-TA3-T	TO-220	G	D	S	Tube
18NM65L-TF1-T	18NM65G-TF1-T	TO-220F1	G	D	S	Tube
18NM65L-TF2-T	18NM65G-TF2-T	TO-220F2	G	D	S	Tube
18NM65L-TF3-T	18NM65G-TF3-T	TO-220F	G	D	S	Tube
18NM65L-TM3-T	18NM65G-TM3-T	TO-251	G	D	S	Tube
18NM65L-TN3-R	18NM65G-TN3-R	TO-252	G	D	S	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

18NM65L-TA3-T
(1) Packing Type
(2) Package Type
(3) Green Package

(1) T: Tube, R: Tape Reel
(2) TA3: TO-220, TF1: TO-220F1, TF2: TO-220F2, TF3: TO-220F, TM3: TO-251, TN3: TO-252
(3) L: Lead Free, G: Halogen Free and Lead Free

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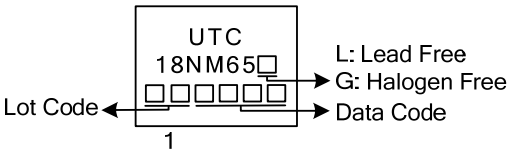
■ MARKING



■ ABSOLUTE MAXIMUM RATINGS (T_C = 25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	650	V
Gate-Source Voltage		V_{GSS}	±30	V
Drain Current	Continuous	I_D	18	A
	Pulsed (Note 2)	I_{DM}	72	A
Avalanche Current (Note 2)		I_{AR}	2.9	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	560	mJ
	Repetitive	E_{AR}	0.44	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	6.0	V/ns
Power Dissipation	TO-220	P_D	235	W
	TO-220F/ TO-220F1 TO-220F2		390	W
	TO-251/TO-252		357	W
Junction Temperature		T_J	+150	°C
Storage Temperature		T_{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
2. Repetitive Rating : Pulse width limited by maximum junction temperature.
3. L = 133 mH, I_{AS} = 2.9A, V_{DD} = 50V, R_G = 25 Ω, Starting T_J = 25°C
4. I_{SD}≤18A, di/dt≤200A/μs, V_{DD}≤BV_{DSS}, Starting T_J = 25°C

■ THERMAL DATA

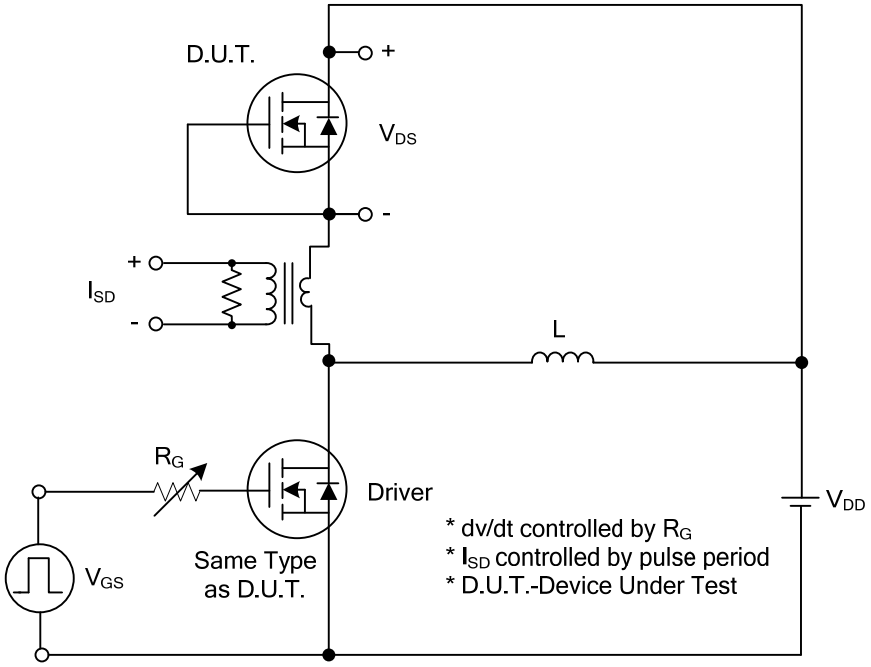
PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient	TO-220/TO-220F TO-220F1/TO-220F2	θ_{JA}	62.5	°C/W
	TO-251/TO-252		110	°C/W
Junction to Case	TO-220	θ_{JC}	0.53	°C/W
	TO-220F/TO-220F1 TO-220F2		5	°C/W
	TO-251/TO-252		1.79	°C/W

■ ELECTRICAL CHARACTERISTICS (T_J =25°C, unless otherwise specified)

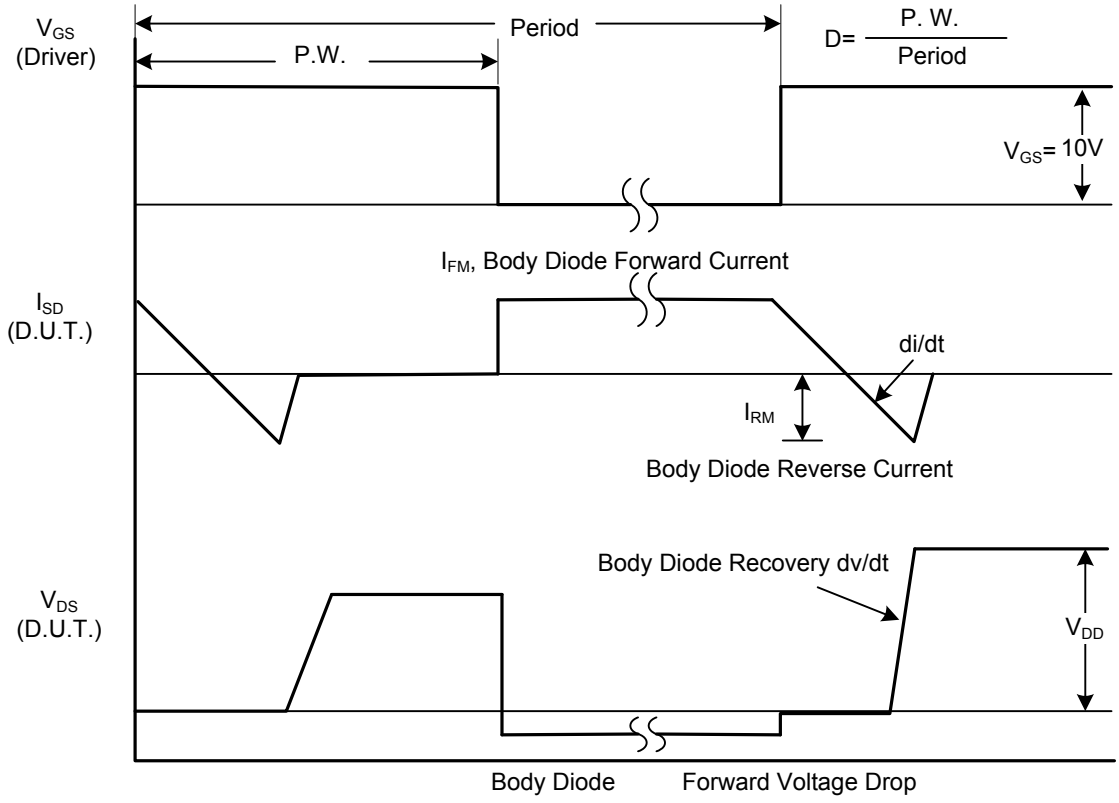
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V, I_D=250μA	650			V
Drain-Source Leakage Current	I_{DSS}	V_{DS}=650V, V_{GS}=0V			10	μA
Gate-Body Leakage Current	I_{GSS}	V_{DS}=0V, V_{GS}=±30V			±100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	V_{DS}=V_{GS}, I_D=250μA	2.5		4.5	V
Static Drain-Source On-Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=9.0A		0.28	0.33	Ω
DYNAMIC PARAMETERS						
Input Capacitance	C_{ISS}	V_{GS}=0V, V_{DS}=25V, f=1.0MHz		1100	1650	pF
Output Capacitance	C_{OSS}			750	1125	pF
Reverse Transfer Capacitance	C_{RSS}			33	65	pF
Gate Resistance	R_G	f =1MHz, Open Drain			5	Ω
SWITCHING PARAMETERS						
Total Gate Charge (Note 1)	Q_G	V_{GS}=10V, V_{DS}=50V_{DSS}, I_D=1.3A, I_G=100μA		128	190	nC
Gate Source Charge	Q_{GS}			9	13	nC
Gate Drain Charge	Q_{GD}			27	36	nC
Turn-ON Delay Time (Note 1)	$t_{D(ON)}$	V_{GS}=10V, V_{DS}=30V_{DSS}, I_D=0.5A, R_G=25Ω (External)		64	86	ns
Turn-ON Rise Time	t_R			152	190	ns
Turn-OFF Delay Time	$t_{D(OFF)}$			372	558	ns
Turn-OFF Fall-Time	t_F			164	240	ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Maximum Continuous Drain-Source Diode Forward Current	I_S				18	A
Maximum Pulsed Drain-Source Diode Forward Current	I_{SM}				72	A
Drain-Source Diode Forward Voltage (Note 1)	V_{SD}	I_F=I_S ,V_{GS}=0V			1.5	V
Reverse Recovery Time (Note 1)	t_{rr}	I_S=18A, V_{GS}=0V, dI_F/dt=100A/μs		420		ns
Reverse Recovery Charge	Q_{rr}			7.0		μC

Notes: 1. Pulse Test : Pulse width ≤ 300μs, Duty cycle ≤ 2%.
2. Essentially independent of operating ambient temperature.

■ TEST CIRCUITS AND WAVEFORMS

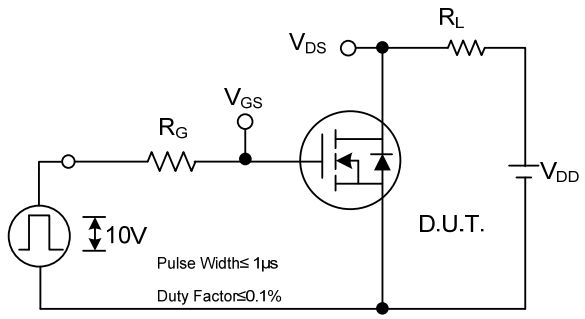


Peak Diode Recovery dv/dt Test Circuit

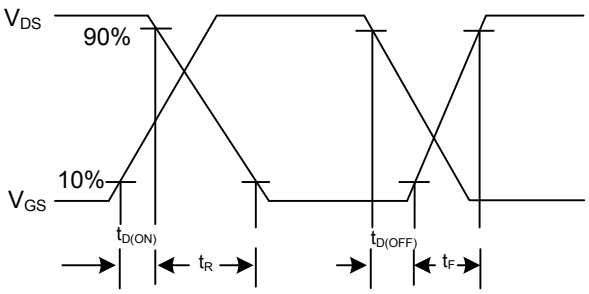


Peak Diode Recovery dv/dt Waveforms

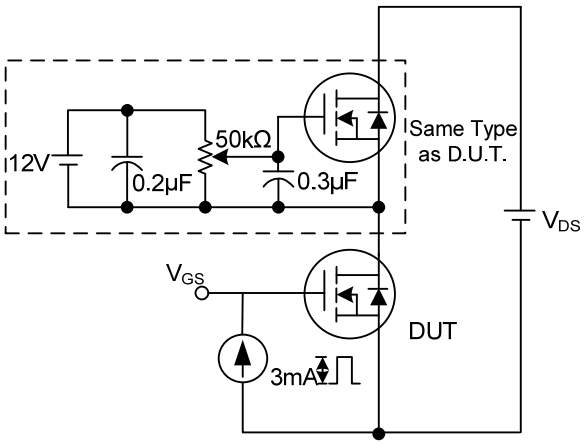
■ TEST CIRCUITS AND WAVEFORMS (Cont.)



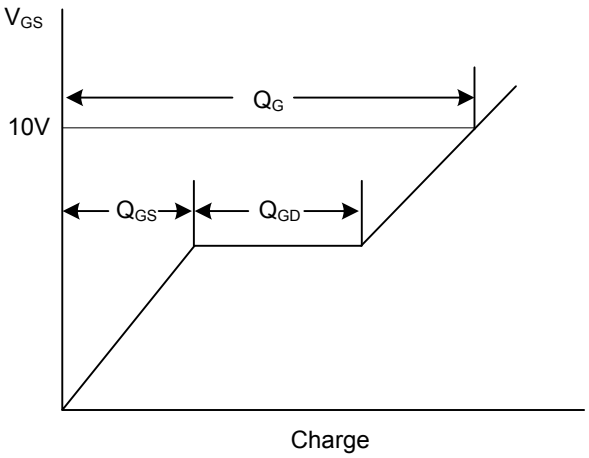
Switching Test Circuit



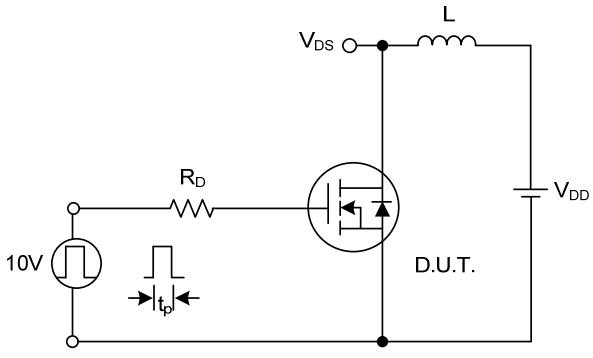
Switching Waveforms



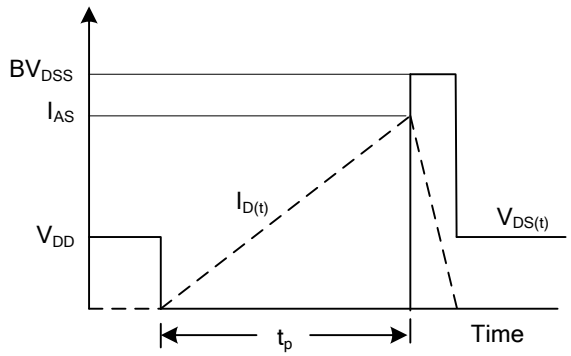
Gate Charge Test Circuit



Gate Charge Waveform



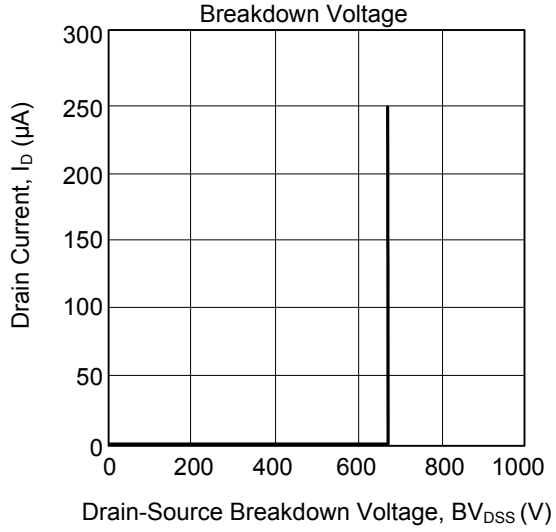
Unclamped Inductive Switching Test Circuit



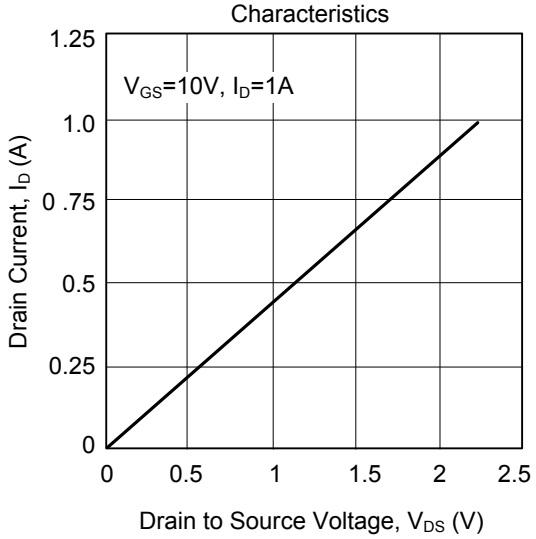
Unclamped Inductive Switching Waveforms

■ TYPICAL CHARACTERISTICS

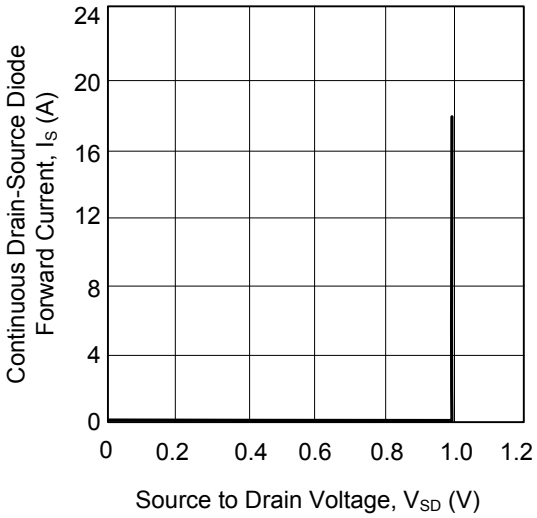
Drain Current vs. Drain-Source Breakdown Voltage



Drain-Source On-State Resistance Characteristics



Continuous Drain-Source Diode Forward Current vs. Source to Drain Voltage



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